

Supporting Information

Isolation and Identification of Post-Transcriptional Gene Silencing-Related Micro-RNAs by Functionalized Silicon Nanowire Field-effect Transistor

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Table S1. Predicted pre-miRNAs yielding the paired sRNAs

No.	miRNA ID	Location ^a (nucleotide)	Reads ^b				<i>N. benthamiana</i> genomic contig ID
			Total		Eluted		
			5'- strand	3'- strand	5'- strand	3'- strand	
1	21956	16326-16385	23	299	36	79	Niben044Scf00022111
2	140486	3698-3783	4	207	39	49	Niben044ctg26199327
3	32913	9345-9438	401	628	62	108	Niben044scf00033254
4	21409	9750-9883	428	50231	35	16420	Niben044scf0021673
5	6873	64319-64586	194	24	172	117	Niben044scf00006983
6	37443	31216-31573	6570	924	3703	235	Niben044scf0037814
7	16712	52681-53224	71	0	54	30	Niben044scf00016874
8	11818	238382-239250	2	3	36	44	Niben044scf00011819
9	20111	3622-4500	0	189	33	91	Niben044scf00020348

^aThe position of the predicted miRNA gene bases on the sequence of the genomic contigs of *Nicotiana benthamiana*.

^bThe number of each sRNAs sequenced in the total and eluted sRNA.

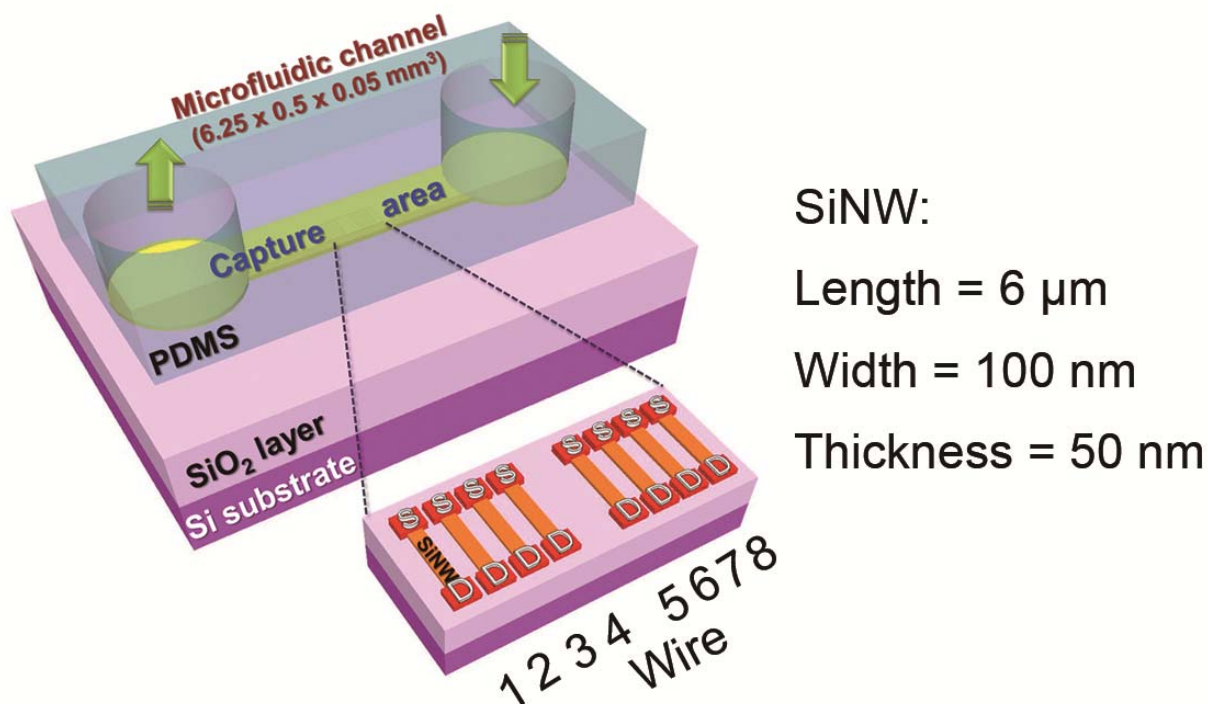


Figure S1. An illustrative representation of eight SiNW-FET devices and the capture area on an SOI chip.

The eight SiNW-FETs are labelled in numerical order. The capture area beneath the PDMS microfluidic channel covers not only minute SiNW-FET surfaces but also the vast surrounding substrate surface. Because a SiO₂ layer was coated on the capture area, the immobilization of receptors (e.g., DNA^{probe} and p19 in this study), the binding of targets (miRNA and ds-sRNA), and the elution of the receptor-target complexes (DNA-miRNA and p19-ds-sRNA) occurred on the entire region of the capture area.

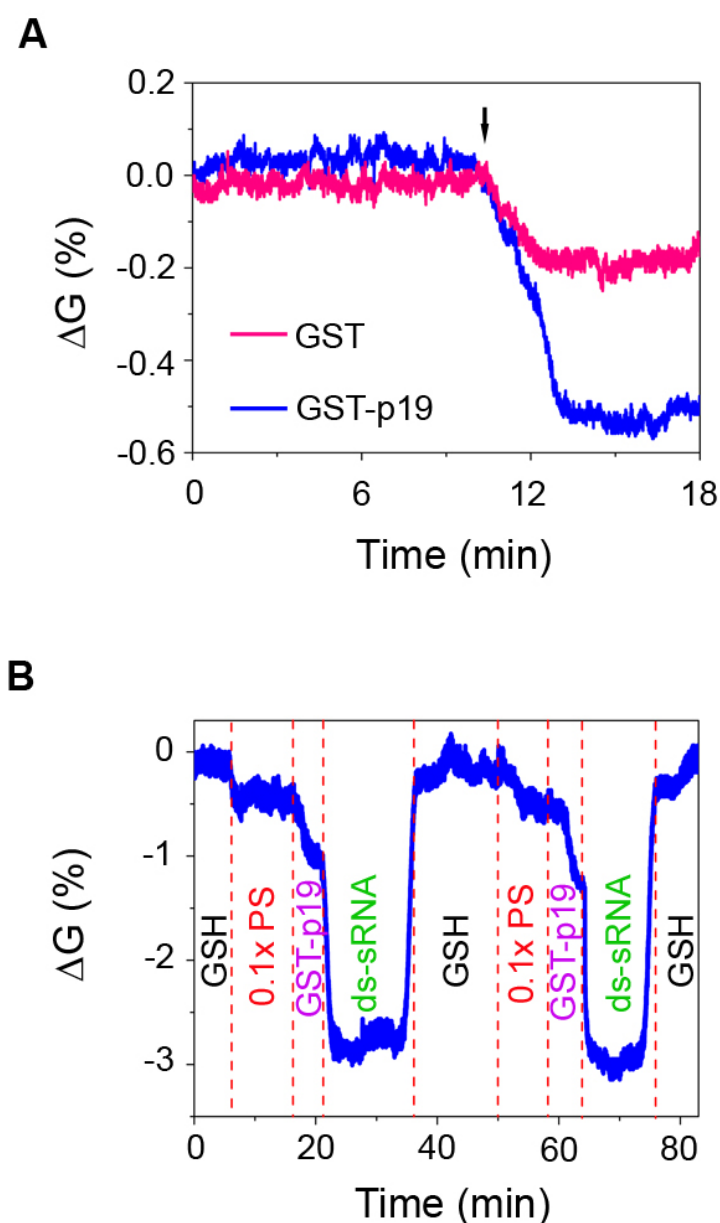


Figure S2. The binding tests of ds-sRNAs to a p19/SiNW-FET.

(A). The electrical conductance changes (ΔG s) of a GSH/SiNW-FET responded to the associations of GST (red trace) and GST-p19 (blue trace), respectively. (B). A reusable SiNW-FET biosensor was demonstrated by the reproducibility of the electrical conductance changes (ΔG s) of a GSH/SiNW-FET endured in the two complete cycles of GSH washing, 0.1 \times PS flushing, GST-p19 immobilization, and ds-sRNA binding. The reproducible ΔG at each repeated step demonstrated the operating stability and device reusability of the SiNW-FET system.

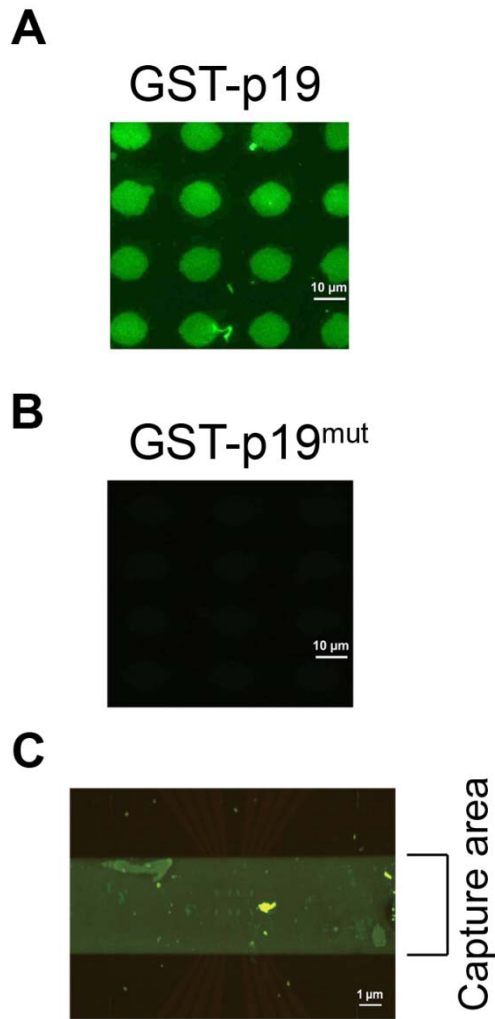


Figure S4. Successful surface modification proved by fluorescence imaging examination.

(A). Binding of 21-nucleotide ds-sRNA to the p19-modified micropatterns. Green fluorescence indicates the successful association of 5'-fluorescein isothiocyanate (FITC)-ds-sRNAs with the p19-modified micropatterns. (B). No fluorescence could be observed for the 21-nucleotide ds-sRNA binding to the p19^{mut}-modified micropatterns, suggesting that the four mutated amino acids of p19^{mut} are crucial to the binding of the ds-sRNA. (C). Visualization of the ds-sRNA captured by p19 over the entire capture area (as illustrated in Figure S1). Green fluorescence indicates that 5'-FITC-ds-sRNAs were captured by the p19 immobilized on the surface of the entire capture area.

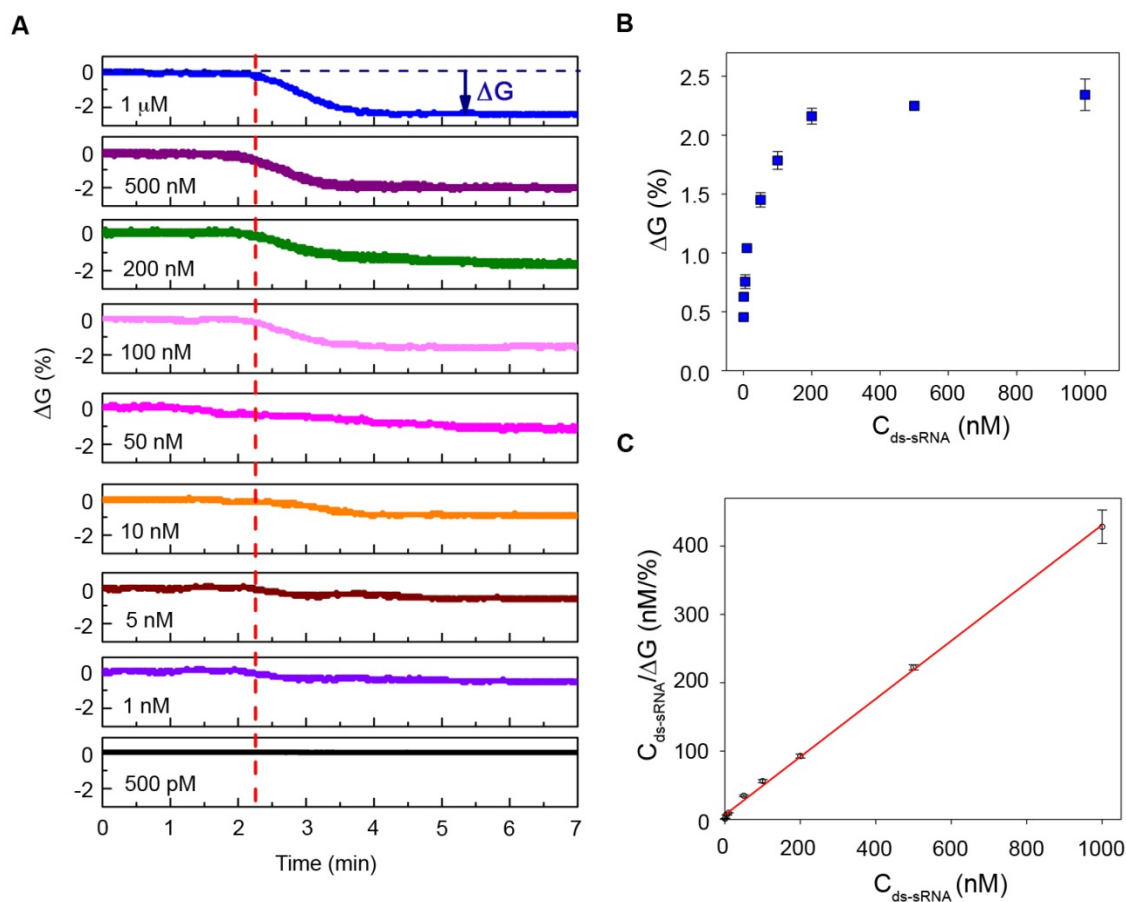


Figure S5. Determination of the dissociation constant (K_d) of the p19-ds-sRNA complex.

(A). The electrical conductance changes (ΔG s) of a p19/SiNW-FET after introducing various concentrations of ds-sRNAs at 500 pM–1 μ M. The vertical red-dotted line indicates the addition of ds-sRNA samples. (B). The ΔG values are presented as a function of ds-sRNA concentration ($C_{ds-sRNA}$) where the data points are taken from (A). (C). A least-squares fit of the $C_{ds-sRNA} / \Delta G$ vs. $C_{ds-sRNA}$. The data points fit to the Langmuir adsorption isotherm model (Eq. 1) yielded $K_d = 15.9 \pm 4.8$ nM for the p19-ds-sRNA complex.

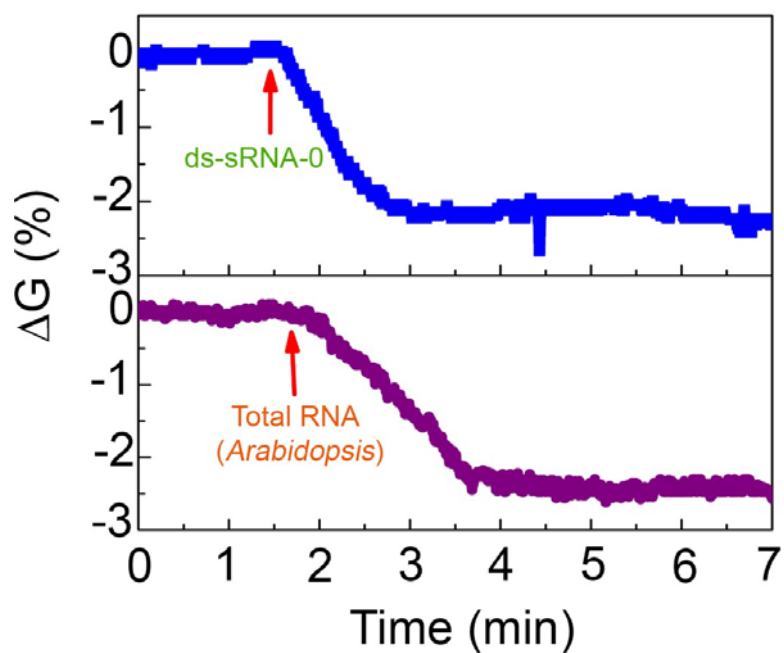


Figure S6. Detections of synthetic ds-sRNAs and total extracted RNA by p19/SiNW-FET.

The normalized ΔG of a p19/SiNW-FET in the detection of (upper panel) synthetic ds-sRNA-0 or (lower panel) the total RNA extracted from *Arabidopsis thaliana*. The decrease of ΔG is due to the gating effect of the negatively charged phosphate backbone of ds-sRNA-0 to the *n*-type p19/SiNW-FET.

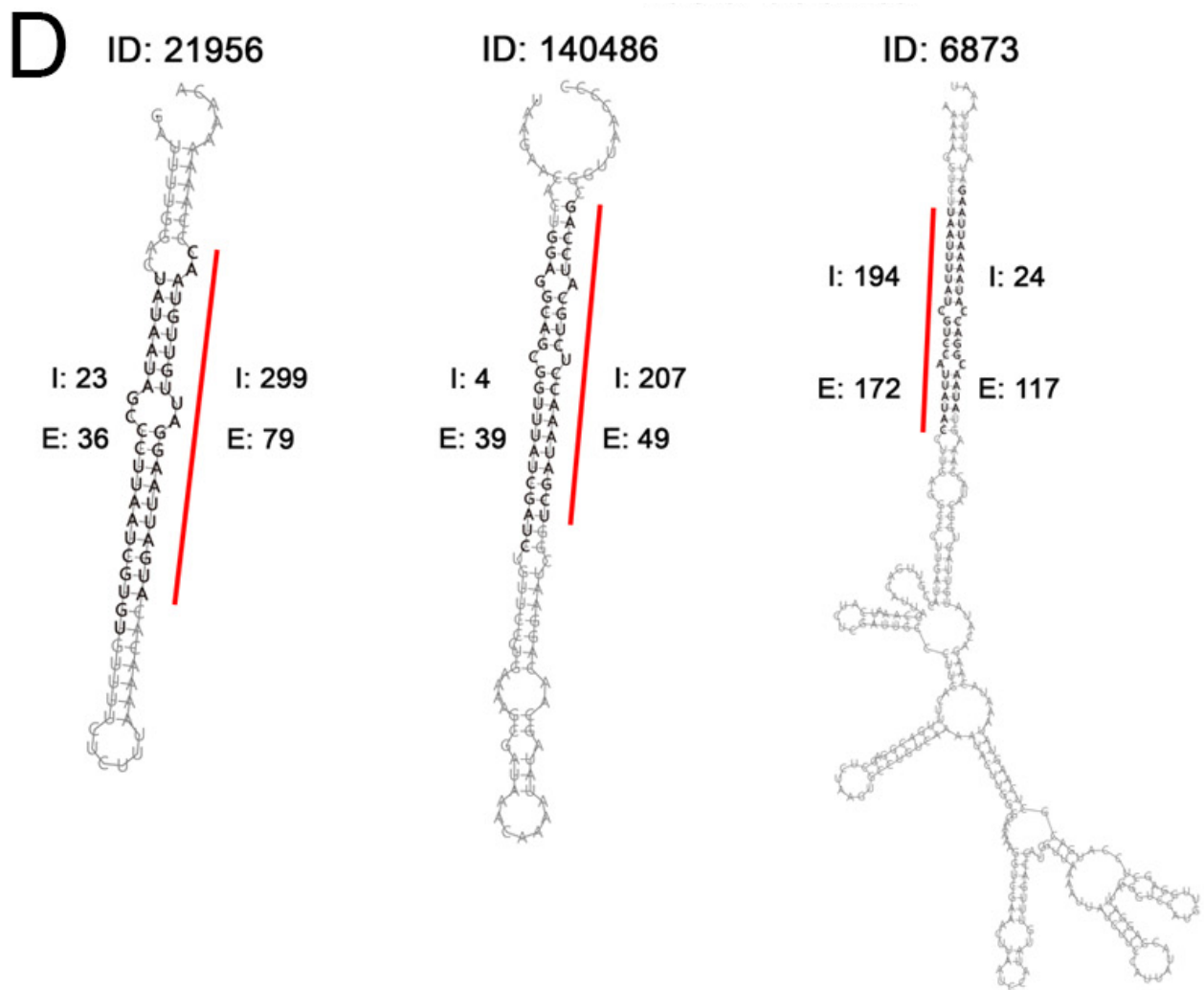


Figure S7. A magnified image of Figure 3D for easier reading.